MANUFACTURE OF THIN FILM TRANSISTOR

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Abstract

PURPOSE:To restrain irregularity of contact resistance between an Al film and a transparent conducting film, and maintain the contact resistance in a small value, regarding the manufacturing method of a thin film transistor which is used for driving the liquid crystal in a liquid crystal display.
CONSTITUTION:A source/drain electrode 33a of a thin film transistor is formed on a transparent substrate 21. As to at least the upper two layers of the electrode 33a is an Al film 31 and a high melting point metal film 30 in the order from the upper layer. An insulating film 35 is formed so as to cover the electrode 33a. An aperture 36b is formed in the insulating film 35 on the electrode 33a. The uppermost Al film 31 of the electrode 33a is etched via the aperture 36b, and the high melting point metal film 30 as the substratum is exposed. A transparent conducting film is formed so as to come into contact with the high melting point metal film 30 in the aperture 36b.